



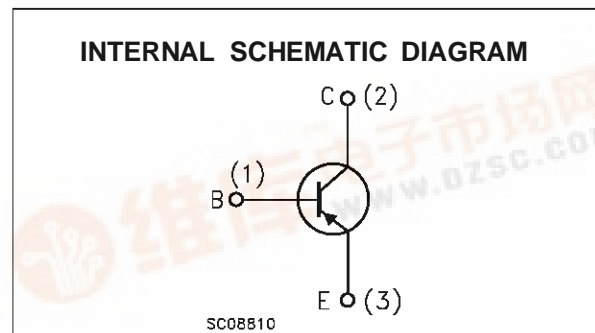
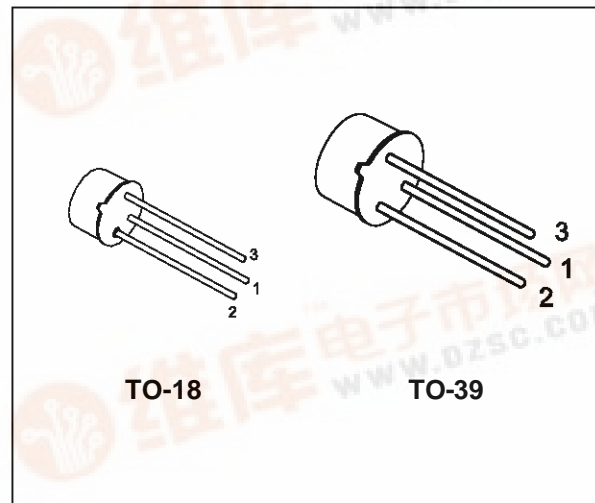
2N2905
2N2907

GENERAL PURPOSE AMPLIFIERS AND SWITCHES

DESCRIPTION

The 2N2905 and 2N2907 are silicon planar epitaxial PNP transistors in Jedec TO-39 (for 2N2905) and in Jedec TO-18 (for 2N2907) metal case. They are designed for high speed saturated switching and general purpose application.

☞ 2N2905 approved to CECC 50002-102,
2N2907 approved to CECC 50002-103
available on request.



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|-----------|---|------------------------|------------------|
| V_{CBO} | Collector-Base Voltage ($I_E = 0$) | -60 | V |
| V_{CEO} | Collector-Emitter Voltage ($I_B = 0$) | -40 | V |
| V_{EBO} | Emitter-Base Voltage ($I_C = 0$) | -5 | V |
| I_C | Collector Current | -0.6 | A |
| P_{tot} | Total Dissipation at $T_{amb} \leq 25^\circ\text{C}$ for 2N2905 for 2N2907 at $T_{case} \leq 25^\circ\text{C}$ for 2N2905 for 2N2907 | 0.6 0.4 3 1.8 | W W W W |
| T_{stg} | Storage Temperature | -65 to 200 | $^\circ\text{C}$ |
| T_j | Max. Operating Junction Temperature | 200 | $^\circ\text{C}$ |

2N2905/2N2907

THERMAL DATA

| | | TO-39 | TO-18 | |
|-----------------------|-------------------------------------|-------|-------|------|
| R _{thj-case} | Thermal Resistance Junction-Case | Max | 58.3 | °C/W |
| R _{thj-amb} | Thermal Resistance Junction-Ambient | Max | 292 | °C/W |

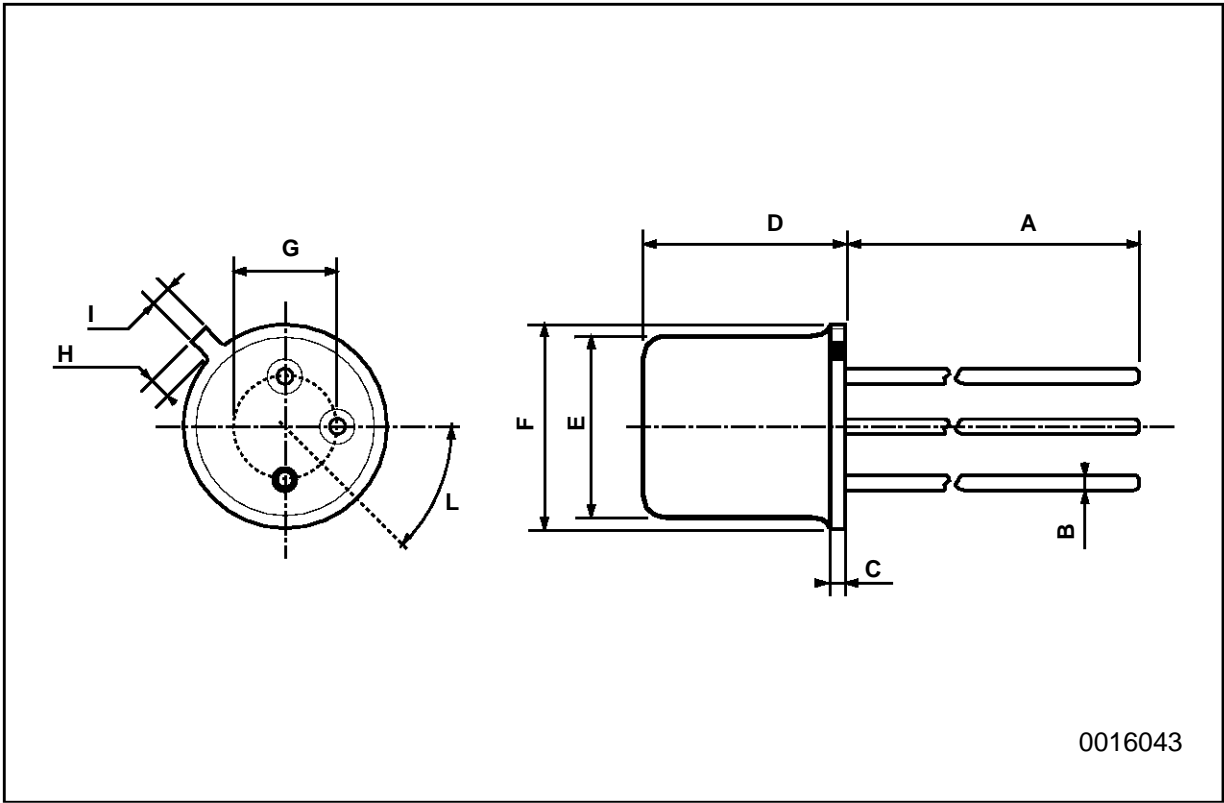
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|------------------------|--|---|-----------------------------|------|--------------|----------|
| I _{CBO} | Collector Cut-off Current (I _E = 0) | V _{CB} = -50 V V _{CB} = -50 V T _{case} = 150 °C | | | -20 -20 | nA μA |
| I _{CEX} | Collector Cut-off Current (V _{BE} = -0.5V) | V _{CE} = -30 V | | | -50 | nA |
| I _{BEX} | Base Cut-off Current (V _{BE} = -0.5V) | V _{CE} = -30 V | | | -50 | nA |
| V _{(BR)CBO} * | Collector-Base Breakdown Voltage (I _E = 0) | I _C = -10 μA | -60 | | | V |
| V _{(BR)CEO} * | Collector-Emitter Breakdown Voltage (I _B = 0) | I _C = -10 mA | -40 | | | V |
| V _{(BR)EBO} * | Emitter-Base Breakdown Voltage (I _C = 0) | I _E = -10 μA | -5 | | | V |
| V _{CE(sat)} * | Collector-Emitter Saturation Voltage | I _C = -150 mA I _B = -15 mA I _C = -500 mA I _B = -50 mA | | | -0.4 -1.6 | V V |
| V _{BE(sat)} * | Base-Emitter Saturation Voltage | I _C = -150 mA I _B = -15 mA I _C = -500 mA I _B = -50 mA | | | -1.3 -2.6 | V V |
| h _{FE} * | DC Current Gain | I _C = -0.1 mA V _{CE} = -10 V I _C = -1 mA V _{CE} = -10 V I _C = -10 mA V _{CE} = -10 V I _C = -150 mA V _{CE} = -10 V I _C = -500 mA V _{CE} = -10 V | 35 50 75 100 30 | | 300 | |
| f _T | Transition Frequency | V _{CE} = -20 V f = 100 MHz I _C = -50 mA | 200 | | | MHz |
| C _{EBO} | Emitter Base Capacitance | I _C = 0 V _{EB} = -2 V f = 1MHz | | | 30 | pF |
| C _{CBO} | Collector Base Capacitance | I _E = 0 V _{CB} = -10 V f = 1MHz | | | 8 | pF |
| t _d | Delay Time | V _{CC} = -30 V I _C = -150 mA I _{B1} = -15 mA | | | 10 | ns |
| t _r | Rise Time | V _{CC} = -30 V I _C = -150 mA I _{B1} = -15 mA | | | 40 | ns |
| t _s | Storage Time | V _{CC} = -6 V I _C = -150 mA I _{B1} = -I _{B2} = -15 mA | | | 80 | ns |
| t _f | Fall Time | V _{CC} = -6 V I _C = -150 mA I _{B1} = -I _{B2} = -15 mA | | | 30 | ns |

* Pulsed: Pulse duration = 300 μs, duty cycle ≤ 1 %

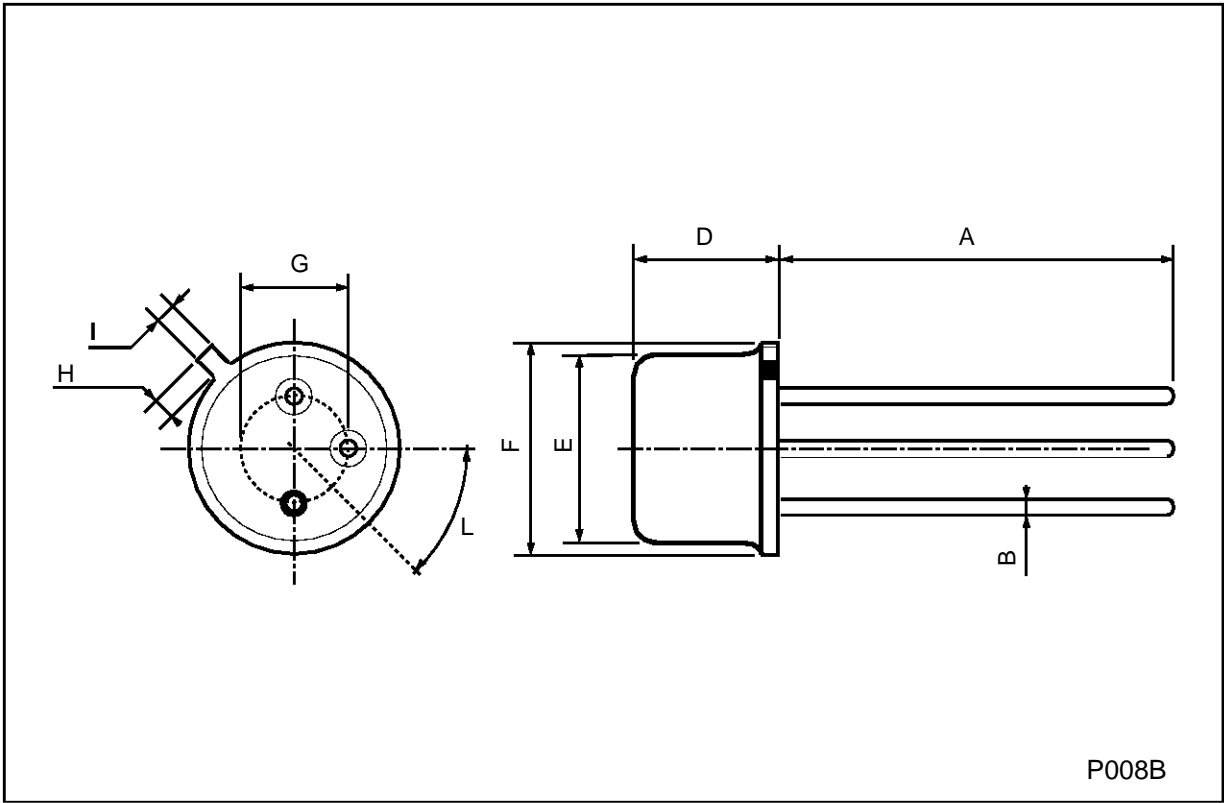
TO-18 MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | | 12.7 | | | 0.500 | |
| B | | | 0.49 | | | 0.019 |
| D | | | 5.3 | | | 0.208 |
| E | | | 4.9 | | | 0.193 |
| F | | | 5.8 | | | 0.228 |
| G | 2.54 | | | 0.100 | | |
| H | | | 1.2 | | | 0.047 |
| I | | | 1.16 | | | 0.045 |
| L | 45° | | | 45° | | |



TO-39 MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|------------|------|------|-------|------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 12.7 | | | 0.500 | | |
| B | | | 0.49 | | | 0.019 |
| D | | | 6.6 | | | 0.260 |
| E | | | 8.5 | | | 0.334 |
| F | | | 9.4 | | | 0.370 |
| G | 5.08 | | | 0.200 | | |
| H | | | 1.2 | | | 0.047 |
| I | | | 0.9 | | | 0.035 |
| L | 45° (typ.) | | | | | |



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